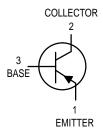
# **High Current Transistors PNP Silicon**



### **MAXIMUM RATINGS**

Rating	Symbol	BC 636	BC 638	BC 640	Unit
Collector-Emitter Voltage	VCEO	-45	-60	-80	Vdc
Collector-Base Voltage	V <sub>СВО</sub>	-45	-60	-80	Vdc
Emitter-Base Voltage	VEBO	-5.0			Vdc
Collector Current — Continuous	IC	-0.5			Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12		Watt mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150			°C

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage* (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)	BC636 BC638 BC640	V(BR)CEO	-45 -60 -80	_ _ _	_ _ _	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = -100 μAdc, I <sub>E</sub> = 0)	BC636 BC638 BC640	V(BR)CBO	-45 -60 -80	_ _ _	_ _ _	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -10 μAdc, I <sub>C</sub> = 0)		V(BR)EBO	-5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_{E} = 0, T_{A} = 125^{\circ}\text{C})$		ICBO	_ _	_ _	-100 -10	nAdc μAdc

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle 2.0%.

BC636 BC638 BC640



## **BC636 BC638 BC640**

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Тур	Max	Unit	
ON CHARACTERISTICS(1)						
DC Current Gain $ \begin{array}{l} (I_{C} = -5.0 \text{ mAdc, } V_{CE} = -2.0 \text{ Vdc)} \\ (I_{C} = -150 \text{ mAdc, } V_{CE} = -2.0 \text{ Vdc)} \\ & \text{BC636} \\ & \text{BC638} \\ & \text{BC640} \\ \\ (I_{C} = -500 \text{ mA, } V_{CE} = -2.0 \text{ V}) \end{array} $	hFE	25 40 40 40 40 25		 250 160 160 	-	
Collector-Emitter Saturation Voltage (IC = -500 mAdc, I <sub>B</sub> = -50 mAdc)	VCE(sat)	_	-0.25 -0.5	-0.5 	Vdc	
Base–Emitter On Voltage (I <sub>C</sub> = -500 mAdc, V <sub>CE</sub> = -2.0 Vdc)	VBE(on)	_	_	-1.0	Vdc	
DYNAMIC CHARACTERISTICS	•					
Current-Gain — Bandwidth Product (IC = -50 mAdc, VCE = -2.0 Vdc, f = 100 MHz)	fT	_	150	_	MHz	
Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	9.0	_	pF	
Input Capacitance (VEB = -0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ib</sub>	_	110	_	pF	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,$  Duty Cycle 2.0%.

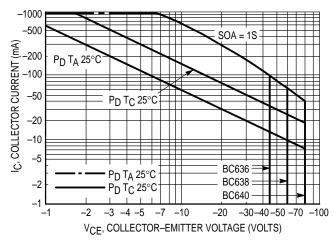


Figure 1. Active Region Safe Operating Area

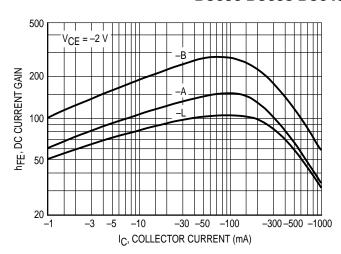


Figure 2. DC Current Gain

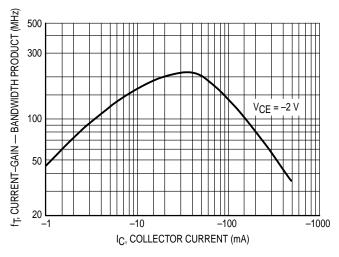


Figure 3. Current Gain Bandwidth Product

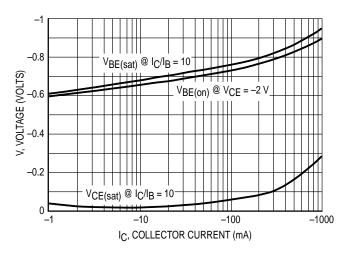
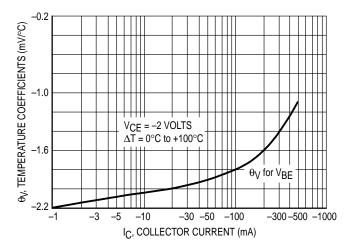
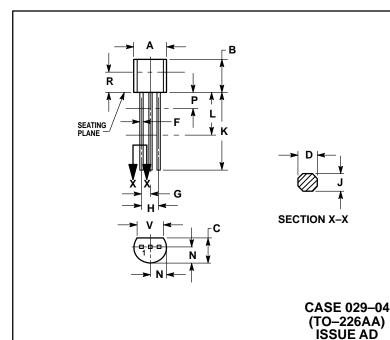


Figure 4. "Saturation" and "On" Voltages



**Figure 5. Temperature Coefficients** 

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
  DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3 43	

STYLE 14:

PIN 1. EMITTER COLLECTOR

BASE

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